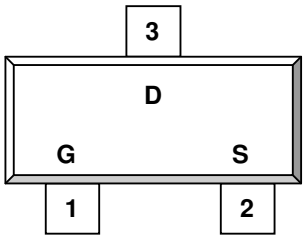
HM2318B

N Channel Enhancement Mode MOSFET

DESCRIPTION

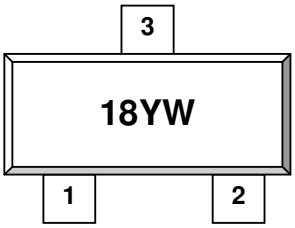
HM2318B is the N-Channel logic enhancement mode power field effect transistor is produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management, other battery powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

PIN CONFIGURATION
SOT-23



1.Gate 2.Source 3.Drain

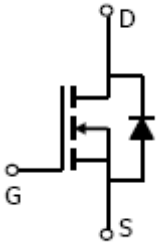
PART MARKING
SOT-23



Y: Year Code W: Week Code

FEATURE

- 40V/3.9A, $R_{DS(ON)}$ = 42mΩ (Typ.) @VGS = 10V
- 40V/3.5A, $R_{DS(ON)}$ = 53mΩ @VGS = 4.5V
- 40V/2.0A, $R_{DS(ON)}$ = 75 mΩ @VGS = 2.5V
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23 package design



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ABSOULTE MAXIMUM RATINGS (Ta = 25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain CurrentTJ=150℃)	T_A=25℃ T_A=70℃	I_D	3.9 3.0	A
Pulsed Drain Current		I_{DM}	10	A
Continuous Source Current (Diode Conduction)		I_S	1.20	A
Power Dissipation	T_A=25℃ T_A=70℃	P_D	1.20 0.8	W
Operation Junction Temperature		T_J	150	℃
Storgae Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	100	℃/W

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ELECTRICAL CHARACTERISTICS (Ta = 25℃ Unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	40			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=VGS,I_D=250uA	0.50		1.2	V
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=40V,V_{GS}=0V			1	uA
		V_{DS}=40V,V_{GS}=0V T_J=85℃			5	
Drain-source On-Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=3.9A V_{GS}=4.5V,I_D=3.5A V_{GS}=2.5V,I_D=2.0A		0.042 0.053 0.075		Ω
Forward Transconductance	g_{fs}	V_{DS}=15V,I_D=6.2A		13		S
Diode Forward Voltage	V_{SD}	I_S=2.3A,V_{GS}=0V		0.8	1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=15V V_{GS}=10V I_D≡2.0A		16	24	nC
Gate-Source Charge	Q_{gs}			3		
Gate-Drain Charge	Q_{gd}			2.5		
Turn-On Time	$t_{d(on)}$	V_{DD}=15V R_L=15Ω I_D=1.0A V_{GEN}=10V R_G=6Ω		15	20	nS
	t_r			6	12	
Turn-Off Time	$t_{d(off)}$			10	20	
	t_f			40	80	

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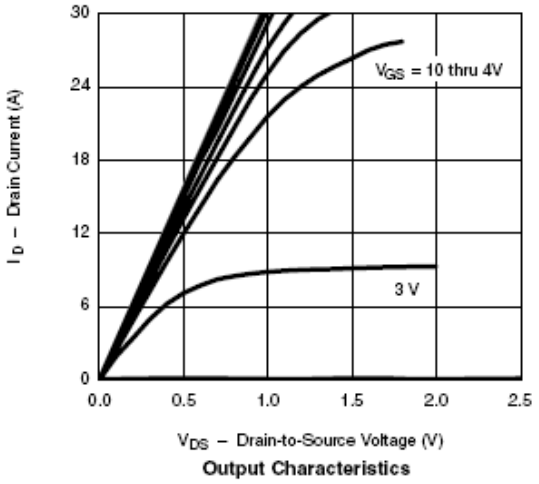
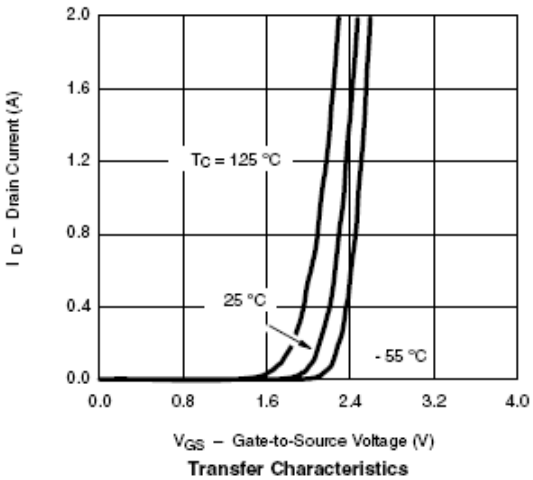
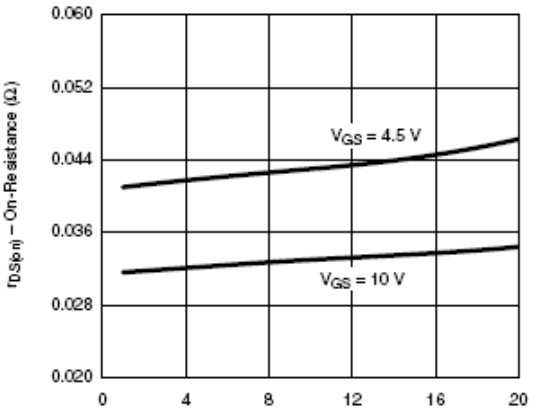
TYPICAL CHARACTERICTICS (25℃ Unless noted)



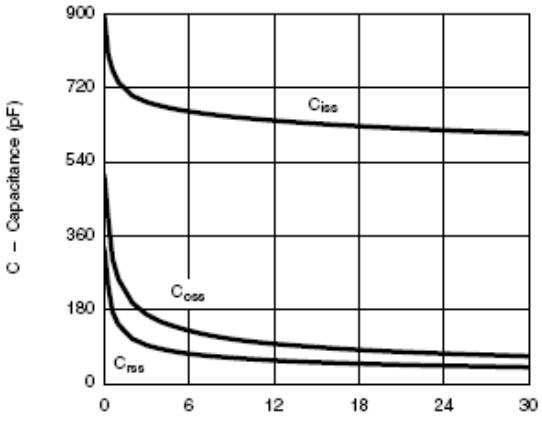
Output Characteristics



Transfer Characteristics

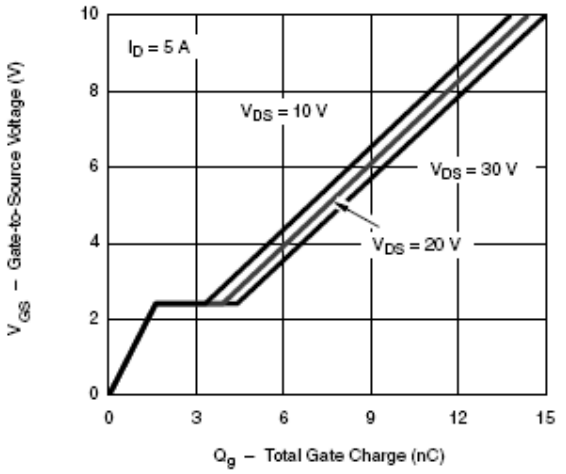


On-Resistance vs. Drain Current and Gate Voltage

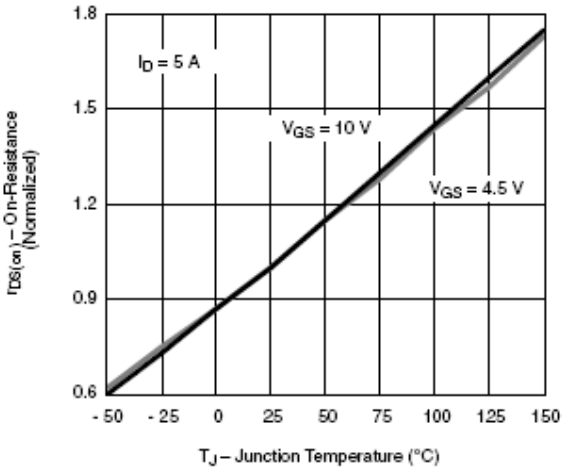


Capacitance

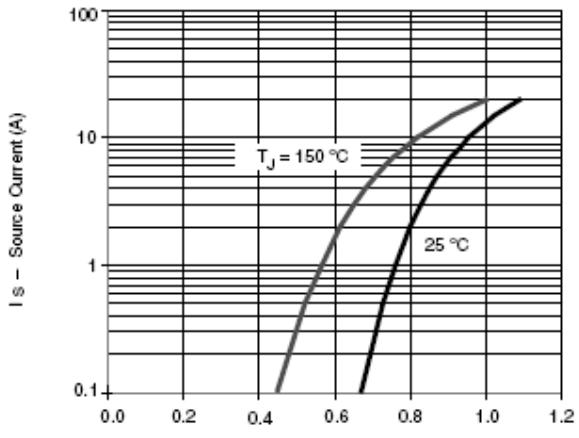
TYPICAL CHARACTERICTICS (25℃ Unless noted)



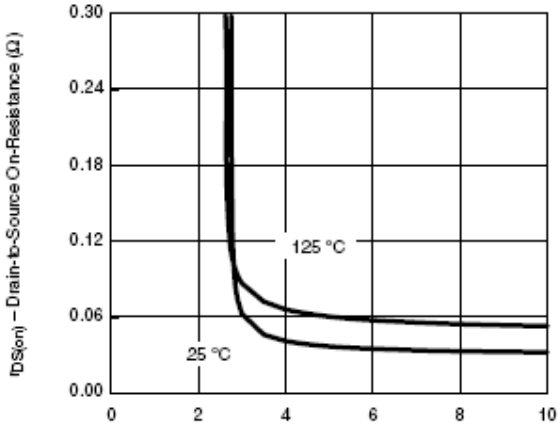
Gate Charge



On-Resistance vs. Junction Temperature

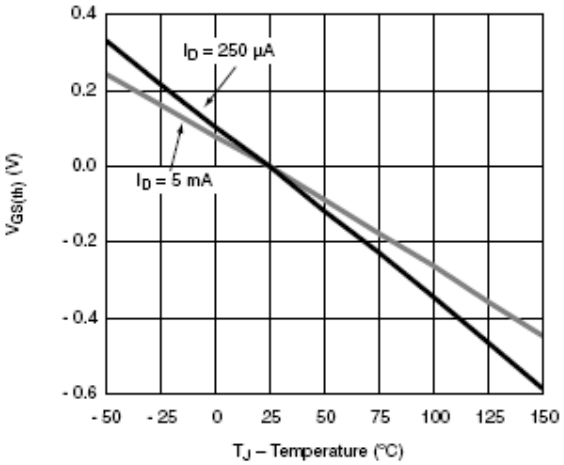


Source-Drain Diode Forward Voltage

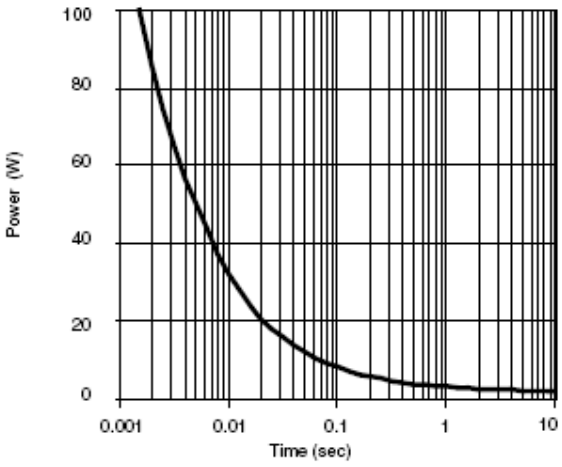


On-Resistance vs. Gate-to-Source Voltage

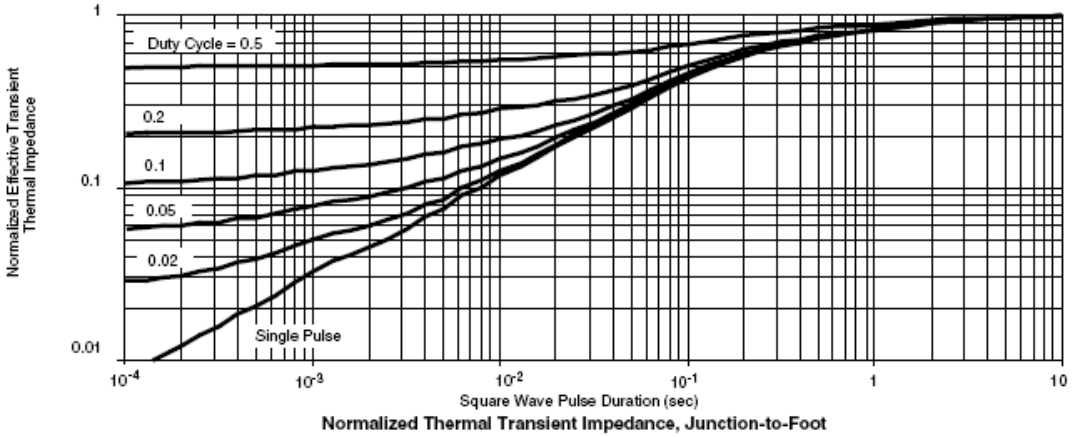
TYPICAL CHARACTERICTICS (25℃ Unless noted)



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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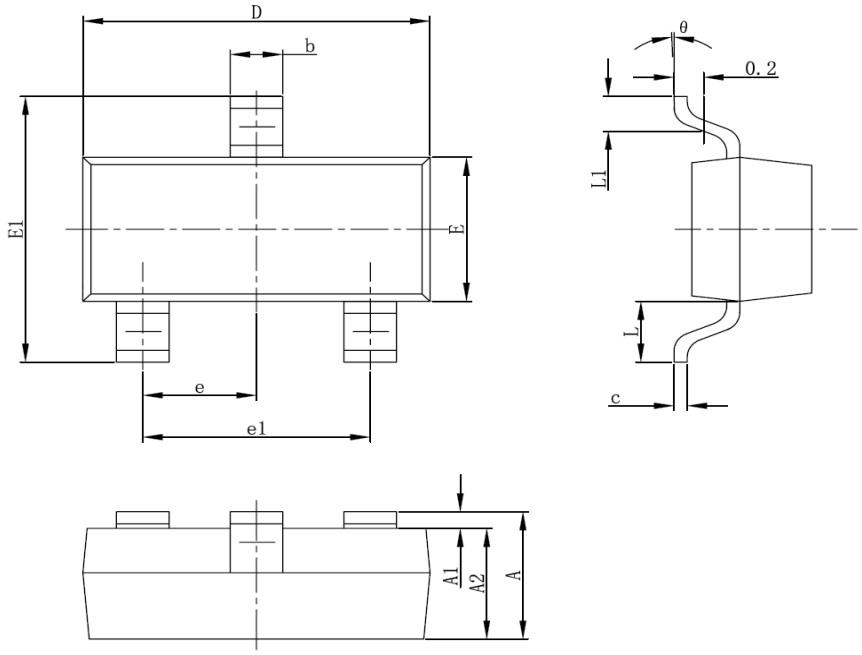
SOT-23 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°